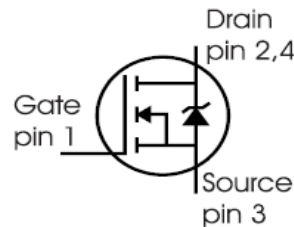
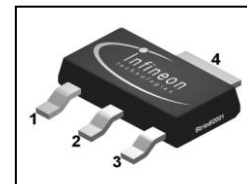


OptiMOS™ Small-Signal-Transistor
Features

- N-channel
- Enhancement mode
- Logic Level (4.5V rated)
- Avalanche rated
- Qualified according to AEC Q101
- 100% lead-free; RoHS compliant
- Halogen-free according to IEC61249-2-21


Product Summary

V_{DS}		100	V
$R_{DS(on),max}$	$V_{GS}=10\text{ V}$	0.23	Ω
	$V_{GS}=4.5\text{ V}$	0.27	
I_D		1.8	A


PG-SOT223


Type	Package	Tape and Reel	Marking	Halogen-Free	Packing
BSP372N	SOT223	H6327: 1000 pcs/ reel	BSP372N	Yes	Non dry

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_A=25\text{ °C}$	1.8	A
		$T_A=70\text{ °C}$	1.5	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ °C}$	7.2	
Avalanche energy, single pulse	E_{AS}	$I_D=1.8\text{ A}$, $R_{GS}=25\ \Omega$	33	mJ
Reverse diode dv/dt	dv/dt	$I_D=1.8\text{ A}$, $V_{DS}=80\text{ V}$, $di/dt=200\text{ A}/\mu\text{s}$, $T_{j,max}=150\text{ °C}$	6	kV/ μs
Gate source voltage	V_{GS}		± 20	V
Power dissipation ¹⁾	P_{tot}	$T_A=25\text{ °C}$	1.8	W
Operating and storage temperature	T_j , T_{stg}		-55 ... 150	°C
ESD Class		JESD22-A114 -HBM	0 (<250V)	
Soldering Temperature			260 °C	
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance junction - soldering point	R_{thJS}		-	-	25	K/W
Thermal resistance junction - ambient	R_{thJA}	minimal footprint	-	-	110	
		6 cm ² cooling area ¹⁾	-	-	70	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}\text{ V}, I_D=218\text{ }\mu\text{A}$	0.8	1.4	1.80	
Drain-source leakage current	I_{DSS}	$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	-	0.1	μA
		$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$	-	-	10	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	10	nA
Gate-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=1.8\text{ A}$	-	153	230	$\text{m}\Omega$
		$V_{GS}=4.5\text{ V}, I_D=1.7\text{ A}$	-	172	270	
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=1.5\text{ A}$		5.1	-	S

¹⁾ Device on 40mm x 40mm x 1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	247	329	pF
Output capacitance	C_{oss}		-	40	54	
Reverse transfer capacitance	C_{rss}		-	19	28	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=1.8\text{ A}, R_{G,ext}=6\ \Omega$	-	5.1	7.7	ns
Rise time	t_r		-	6.7	10.1	
Turn-off delay time	$t_{d(off)}$		-	47.3	71.0	
Fall time	t_f		-	18	27	

Gate Charge Characteristics

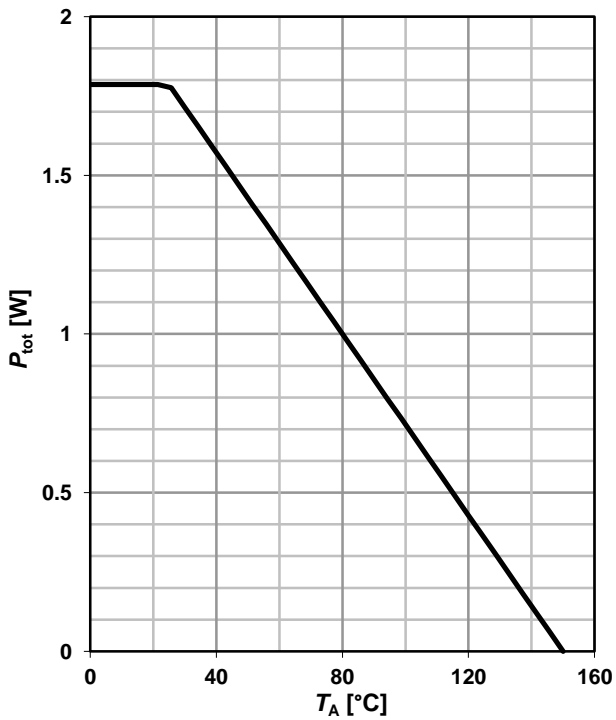
Gate to source charge	Q_{gs}	$V_{DD}=50\text{ V}, I_D=1.8\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	0.6	0.9	nC
Gate to drain charge	Q_{gd}		-	3.0	4.5	
Gate charge total	Q_g		-	9.5	14.3	
Gate plateau voltage	$V_{plateau}$		-	2.3	-	V

Reverse Diode

Diode continuous forward current	I_S	$T_A=25\text{ }^\circ\text{C}$	-	-	1.8	A
Diode pulse current	$I_{S,pulse}$		-	-	7.2	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=1.8\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.82	1.1	V
Reverse recovery time	t_{rr}	$V_R=50\text{ V}, I_F=1.8\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	38	57	ns
Reverse recovery charge	Q_{rr}		-	51.5	77.3	nC

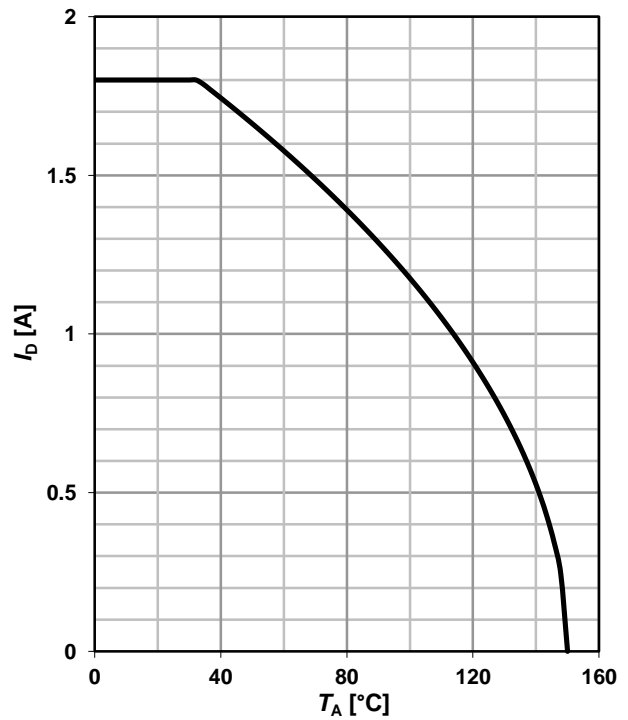
1 Power dissipation

$P_{tot}=f(T_A)$



2 Drain current

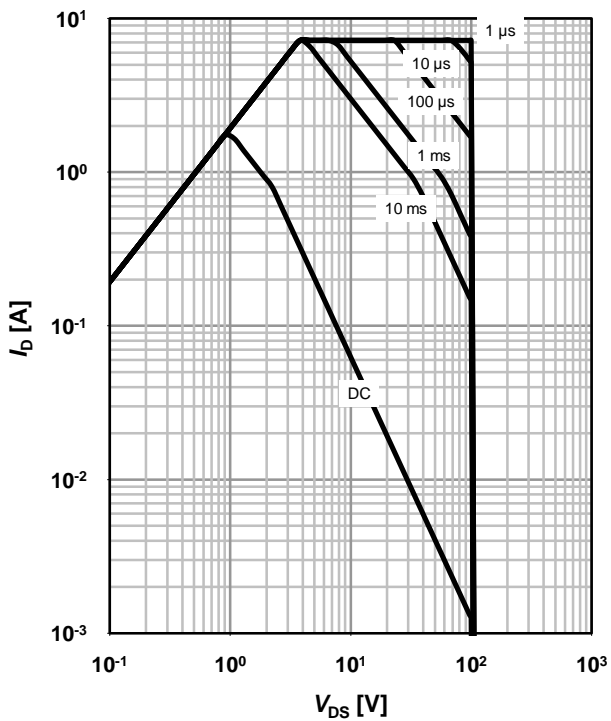
$I_D=f(T_A); V_{GS} \geq 10\text{ V}$



3 Safe operating area

$I_D=f(V_{DS}); T_A=25\text{ °C}; D=0$

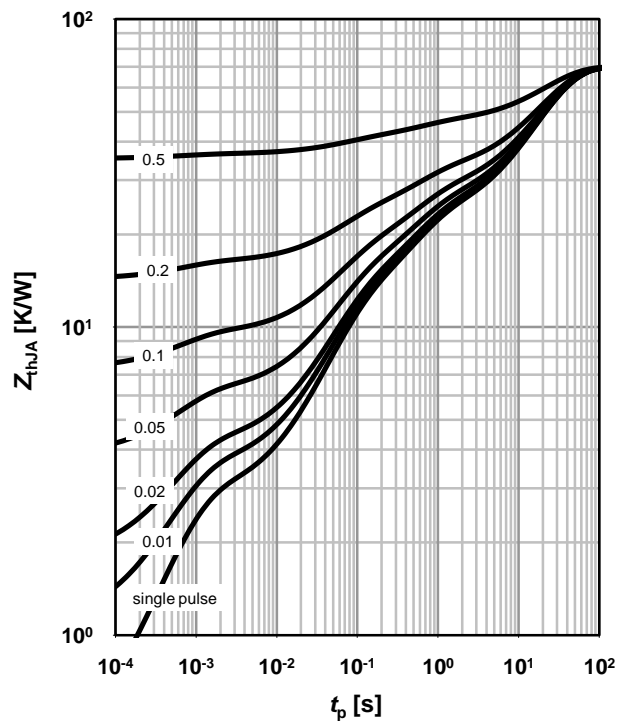
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJA}=f(t_p)$

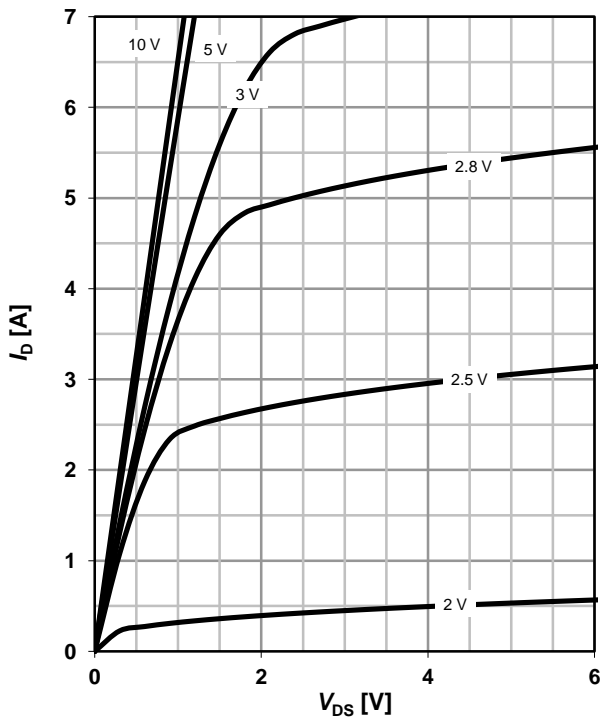
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C}$

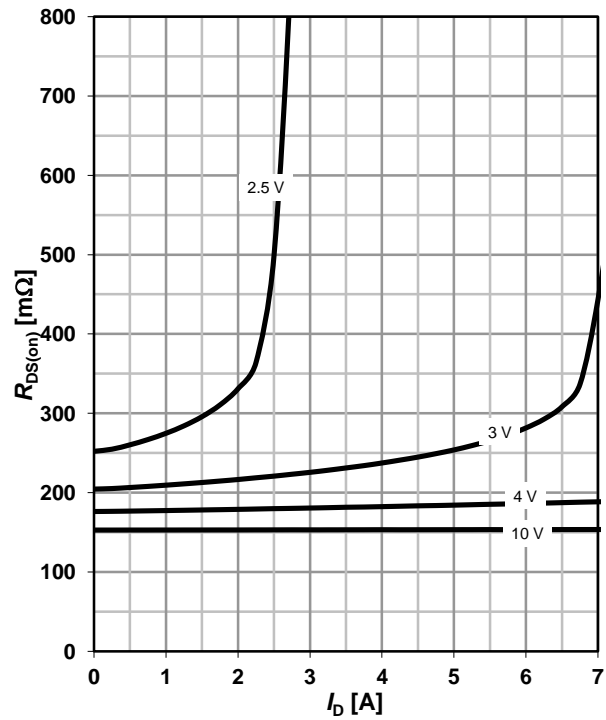
parameter: V_{GS}



6 Typ. drain-source on resistance

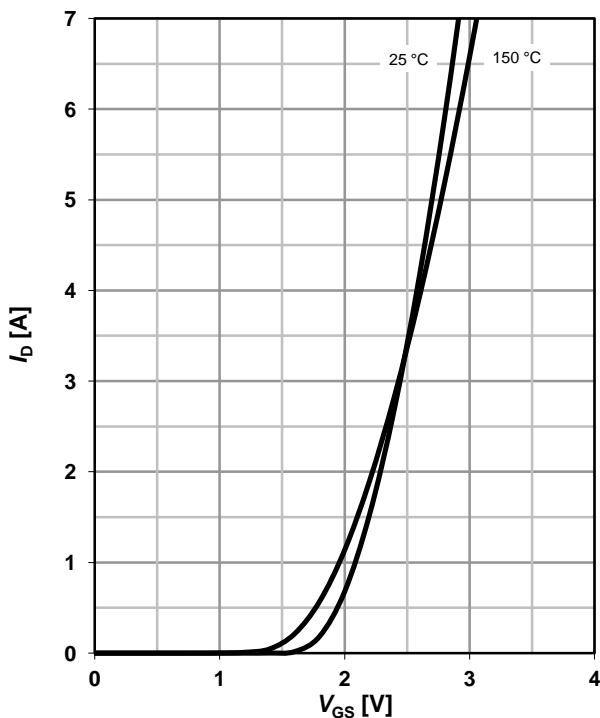
$R_{DS(on)}=f(I_D); T_j=25\text{ }^\circ\text{C}$

parameter: V_{GS}



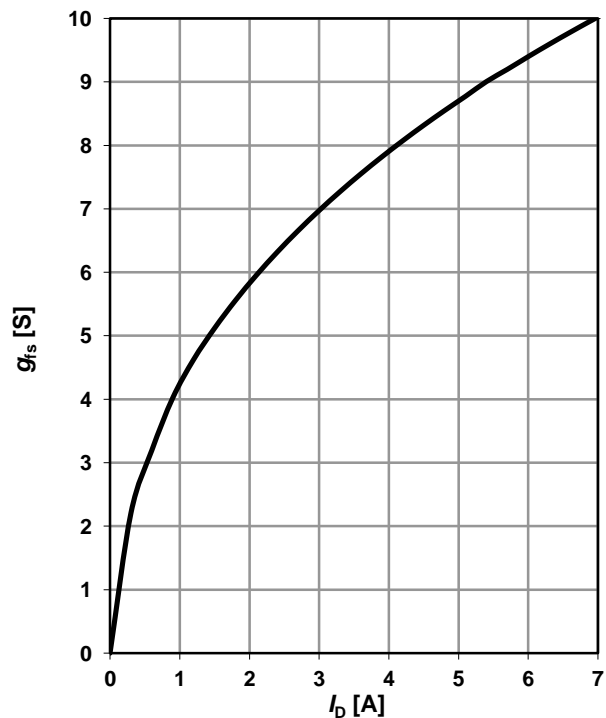
7 Typ. transfer characteristics

$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max}$



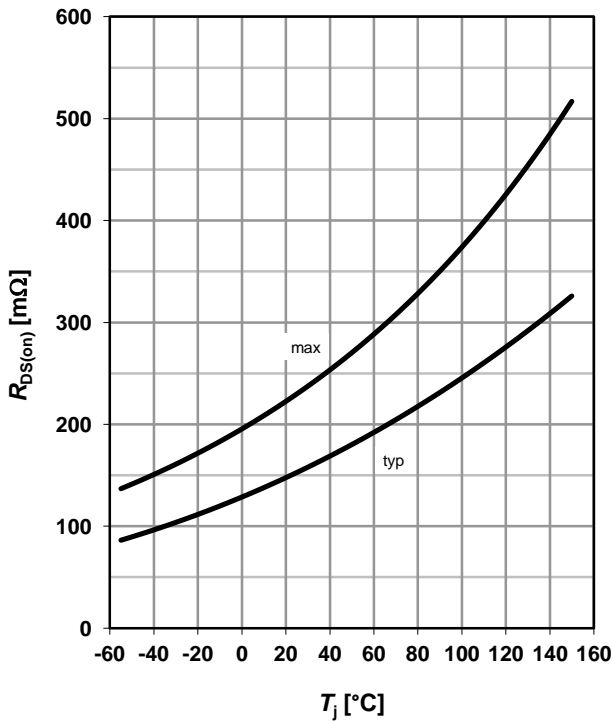
8 Typ. forward transconductance

$g_{fs}=f(I_D); T_j=25\text{ }^\circ\text{C}$



9 Drain-source on-state resistance

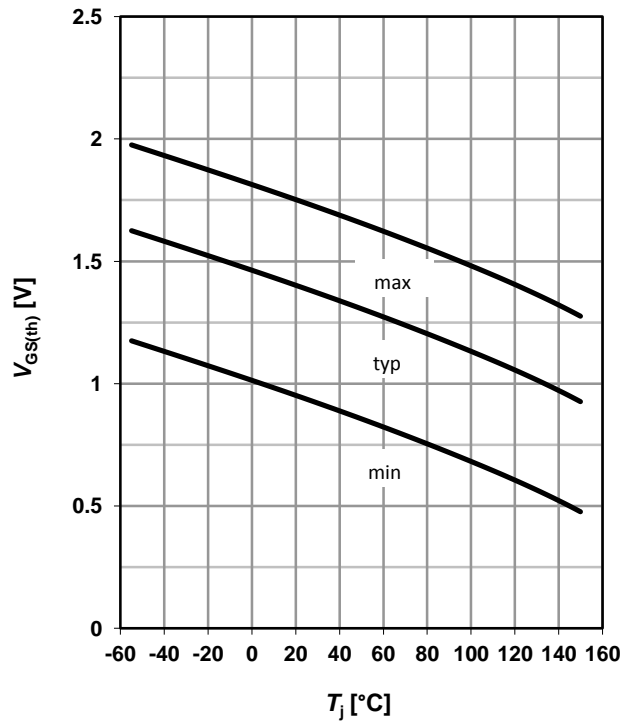
$R_{DS(on)}=f(T_j); I_D=1.8\text{ A}; V_{GS}=10\text{ V}$



10 Typ. gate threshold voltage

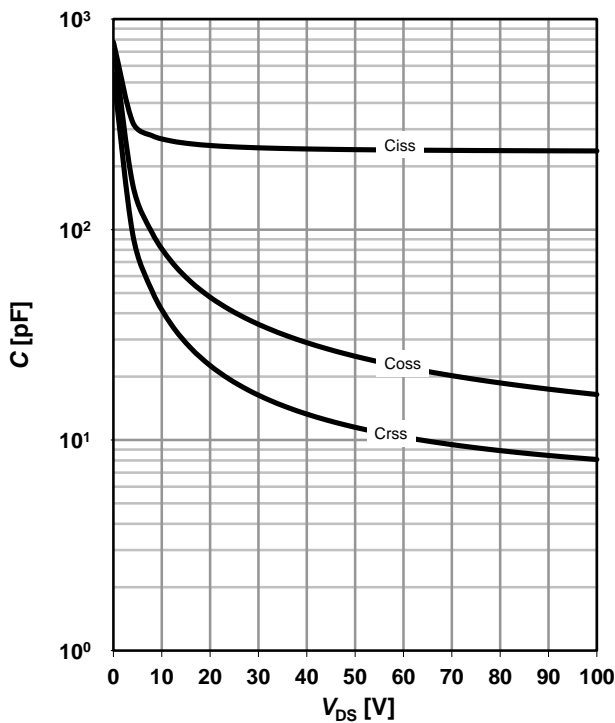
$V_{GS(th)}=f(T_j); V_{DS}=V_{GS}; I_D=218\text{ }\mu\text{A}$

parameter: I_D



11 Typ. capacitances

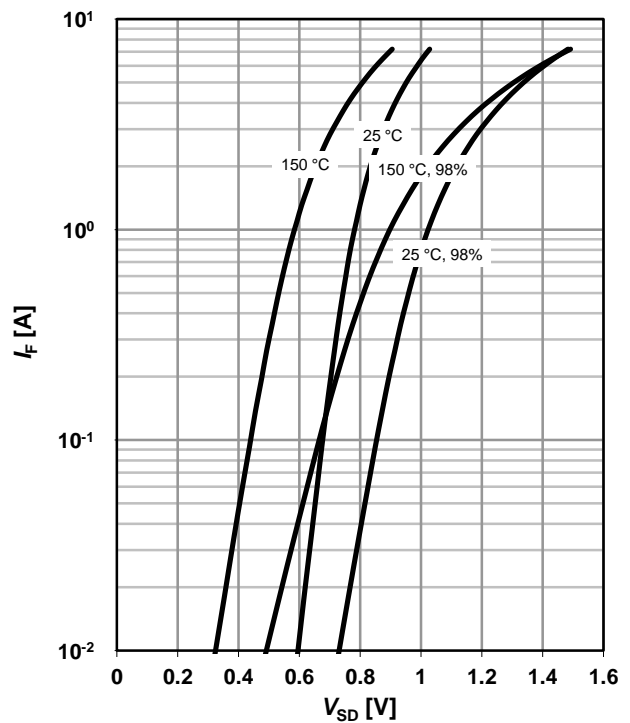
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}; T_j=25^\circ\text{C}$



12 Forward characteristics of reverse diode

$I_F=f(V_{SD})$

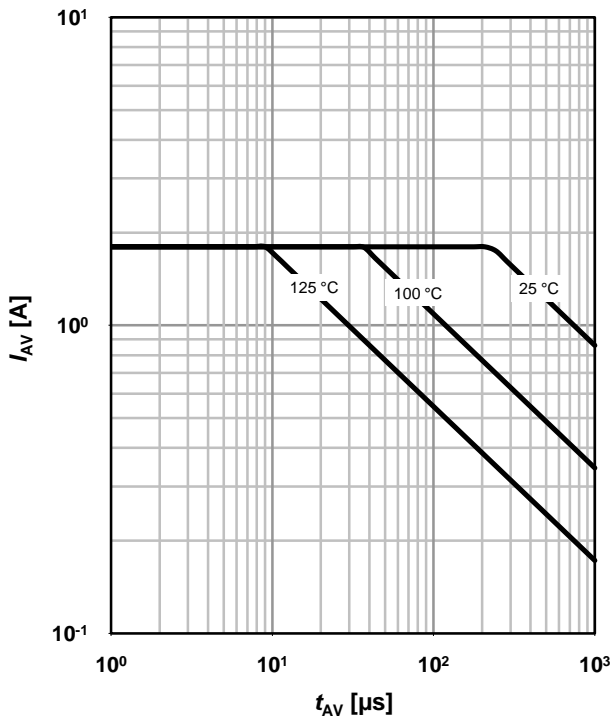
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

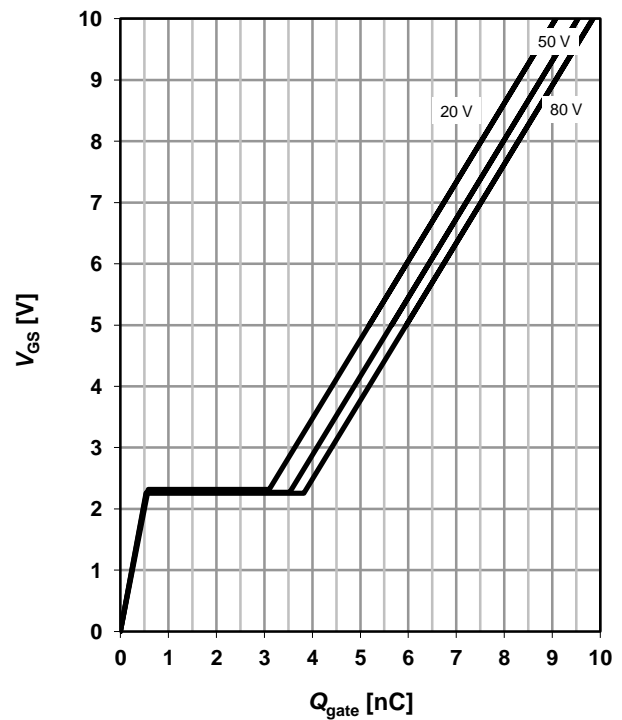
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

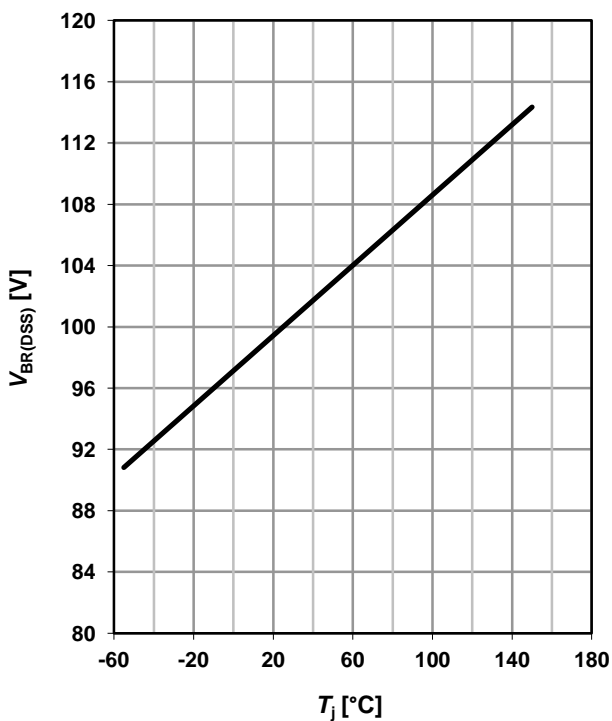
$V_{GS}=f(Q_{\text{gate}}); I_D=1.8 \text{ A pulsed}$

parameter: V_{DD}

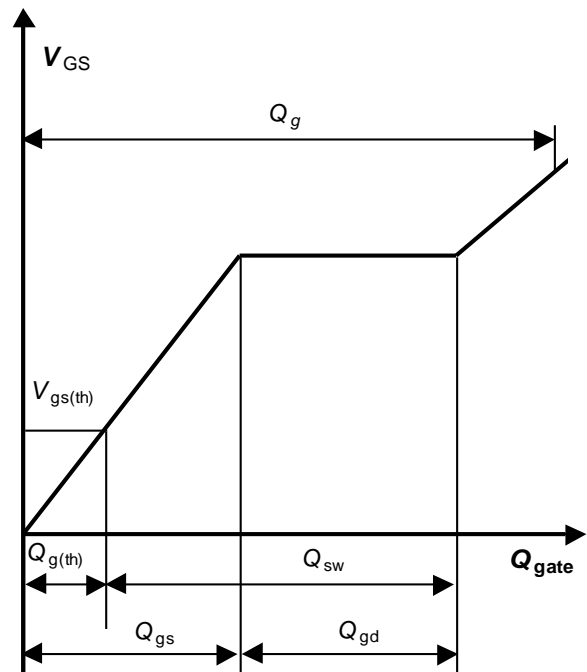


15 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=250 \mu\text{A}$

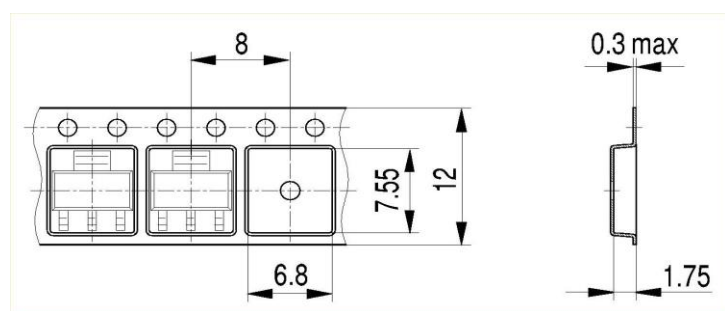
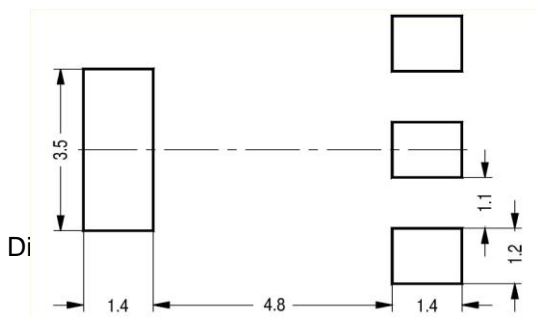
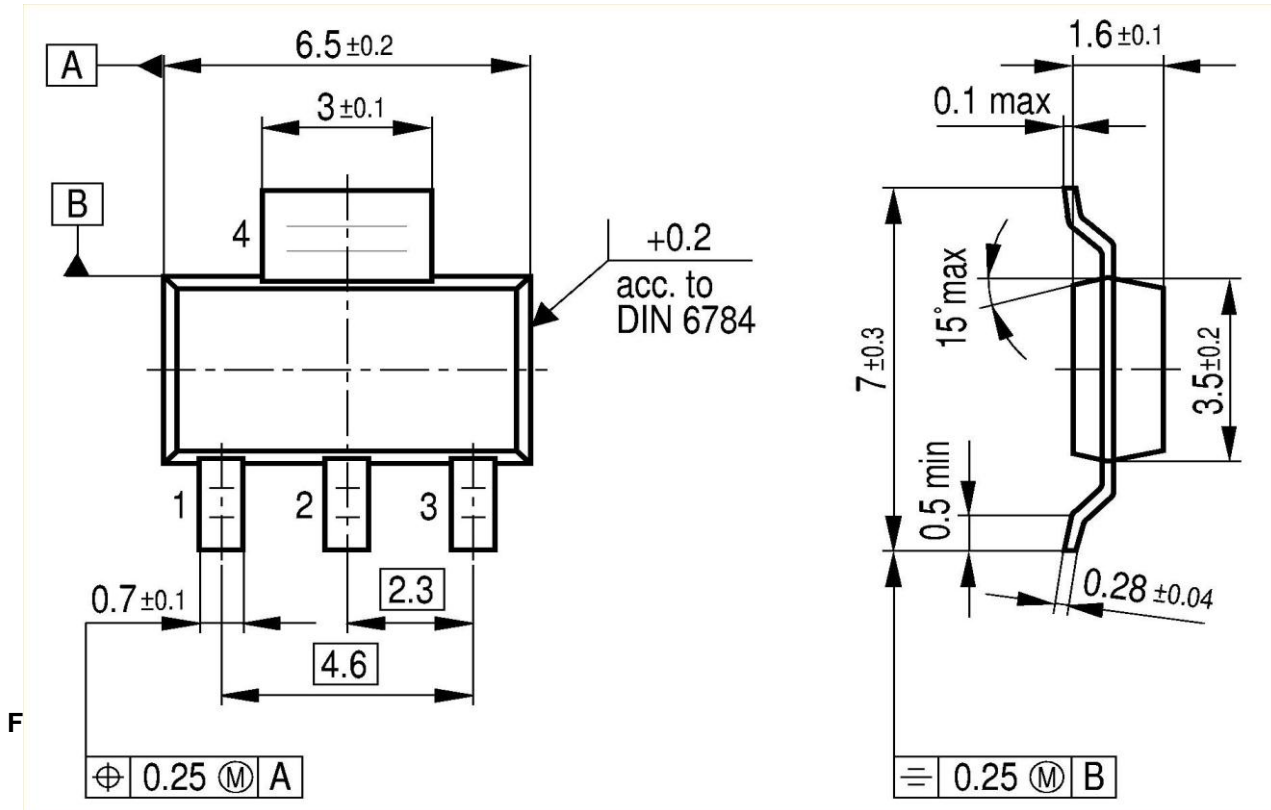


16 Gate charge waveforms



SOT223

Package Outline:



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